HARRIS SEMICONDUCTOR

CD74HC166, CD74HCT166

High Speed CMOS Logic 8-Bit Parallel-In/Serial-Out Shift Register

February 1998

Features

- Buffered Inputs
- Typical f_{MAX} = 50MHz at V_{CC} = 5V, C_L = 15pF, T_A = 25°C
- Fanout (Over Temperature Range)
  - Standard Outputs . . . . . 10 LSTTL Loads
  - Bus Driver Outputs . . . . . 15 LSTTL Loads
- Wide Operating Temperature Range . . . -55°C to 125°C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- HC Types
  - 2V to 6V Operation
  - High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC} at V_{CC} = 5V
- HCT Types
  - 4.5V to 5.5V Operation
  - Direct LSTTL Input Logic Compatibility, V_{IL}= 0.8V (Max), V_{IH} = 2V (Min)
  - CMOS Input Compatibility, $I_I \leq 1\mu A$ at V_{OL}, V_{OH}

Ordering Information

PART NUMBER	TEMP. RANGE (°C)	PACKAGE	PKG. NO.
CD74HC166E	-55 to 125	16 Ld PDIP	E16.3
CD74HCT166E	-55 to 125	16 Ld PDIP	E16.3
CD74HC166M	-55 to 125	16 Ld SOIC	M16.15
CD74HCT166M	-55 to 125	16 Ld SOIC	M16.15
CD54HC166W	-55 to 125	Wafer	

NOTES:

1. When ordering, use the entire part number. Add the suffix 96 to obtain the variant in the tape and reel.
2. Wafer and die is available which meets all electrical specifications. Please contact your local sales office or Harris customer service for ordering information.

Description

The Harris CD74HC166 and the CD74HCT166 8-bit shift register is fabricated with silicon gate CMOS technology. It possesses the low power consumption of standard CMOS integrated circuits, and can operate at speeds comparable to the equivalent low power Schottky device.

The CD74HCT166 is functionally as well as pin compatible with the standard 74LS166.

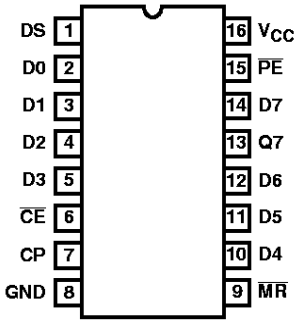
The 166 is an 8-bit shift register that has fully synchronous serial or parallel data entry selected by an active LOW Parallel Enable ($\overline{PE}$) input. When the $\overline{PE}$ is LOW one setup time before the LOW-to-HIGH clock transition, parallel data is entered into the register. When $\overline{PE}$ is HIGH, data is entered into the internal bit position Q0 from Serial Data Input (DS), and the remaining bits are shifted one place to the right (Q0 → Q1 → Q2, etc.) with each positive-going clock transition. For expansion of the register in parallel to serial converters, the Q7 output is connected to the DS input of the succeeding stage.

The clock input is a gated OR structure which allows one input to be used as an active LOW Clock Enable ($\overline{CE}$) input. The pin assignment for the CP and $\overline{CE}$ inputs is arbitrary and can be reversed for layout convenience. The LOW-to-HIGH transition of $\overline{CE}$ input should only take place while the CP is HIGH for predictable operation.

A LOW on the Master Reset ($\overline{MR}$) input overrides all other inputs and clears the register asynchronously, forcing all bit positions to a LOW state.

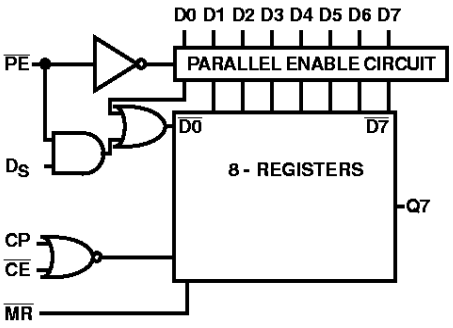
Pinout

CD74HC166, CD74HCT166 (PDIP, SOIC)
TOP VIEW



File Number **1501.1**

Functional Diagram



TRUTH TABLE

INPUTS						INTERNAL Q STATES		OUTPUT
MASTER RESET	PARALLEL ENABLE	CLOCK ENABLE	CLOCK	SERIAL	PARALLEL D0 D7	Q0	Q1	Q7
L	X	X	X	X	X	L	L	L
H	X	L	L	X	X	Q00	Q10	Q0
H	L	L	↑	X	a...h	a	b	h
H	H	L	↑	H	X	H	Q0n	Q6n
H	H	L	↑	L	X	L	Q0n	Q6n
H	X	H	↑	X	X	Q00	Q10	Q70

NOTES:
H = High Voltage Level
L = Low Voltage Level
X = Don't Care
↑ = Transition from Low to High Level
a...h = The level of steady-state input at inputs D0 thru D7, respectively.
Q00, Q10, Q70 = The level of Q0, Q1, or Q7, respectively, before the indicated steady-state input conditions were established.
Q0n, Q6n = The level of Q0 or Q6, respectively, before the most recent ↑ transition of the clock.

Absolute Maximum Ratings

DC Supply Voltage, V_{CC} . . . . . -0.5V to 7V
DC Input Diode Current, I_{IK}
For V_I < -0.5V or V_I > V_{CC} + 0.5V . . . . . ±20mA
DC Output Diode Current, I_{OK}
For V_O < -0.5V or V_O > V_{CC} + 0.5V . . . . . ±20mA
DC Drain Current, per Output, I_O
For -0.5V < V_O < V_{CC} + 0.5V. . . . . ±25mA
DC Output Source or Sink Current per Output Pin, I_O
For V_O > -0.5V or V_O < V_{CC} + 0.5V . . . . . ±25mA
DC V_{CC} or Ground Current, I_{CC} or I_{GND} . . . . . ±50mA

Operating Conditions

Temperature Range (T_A) . . . . . -55°C to 125°C
Supply Voltage Range, V_{CC}
HC Types . . . . . 2V to 6V
HCT Types . . . . . 4.5V to 5.5V
DC Input or Output Voltage, V_I, V_O . . . . . 0V to V_{CC}
Input Rise and Fall Time
2V . . . . . 1000ns (Max)
4.5V. . . . . 500ns (Max)
6V . . . . . 400ns (Max)

Thermal Information

Thermal Resistance (Typical, Note 3)	θ_{JA} (°C/W)
PDIP Package	90
SOIC Package	160

Maximum Junction Temperature . . . . . 150°C
Maximum Storage Temperature Range . . . . . -65°C to 150°C
Maximum Lead Temperature (Soldering 10s) . . . . . 300°C
(SOIC - Lead Tips Only)

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

3. θ_{JA} is measured with the component mounted on an evaluation PC board in free air.

DC Electrical Specifications

PARAMETER	SYMBOL	TEST CONDITIONS		V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
		V_I (V)	I_O (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
HC TYPES												
High Level Input Voltage	V_{IH}	-	-	2	1.5	-	-	1.5	-	1.5	-	V
				4.5	3.15	-	-	3.15	-	3.15	-	V
				6	4.2	-	-	4.2	-	4.2	-	V
Low Level Input Voltage	V_{IL}	-	-	2	-	-	0.5	-	0.5	-	0.5	V
				4.5	-	-	1.35	-	1.35	-	1.35	V
				6	-	-	1.8	-	1.8	-	1.8	V
High Level Output Voltage CMOS Loads	V_{OH}	V_{IH} or V_{IL}	-0.02	2	1.9	-	-	1.9	-	1.9	-	V
			-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
			-0.02	6	5.9	-	-	5.9	-	5.9	-	V
High Level Output Voltage TTL Loads			-4	4.5	3.98	-	-	3.84	-	3.7	-	V
			-5.2	6	5.48	-	-	5.34	-	5.2	-	V
Low Level Output Voltage CMOS Loads	V_{OL}	V_{IH} or V_{IL}	0.02	2	-	-	0.1	-	0.1	-	0.1	V
			0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
			0.02	6	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			4	4.5	-	-	0.26	-	0.33	-	0.4	V
			5.2	6	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I_I	V_{CC} or GND	-	6	-	-	±0.1	-	±1	-	±1	µA

DC Electrical Specifications (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS		V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
		V_I (V)	I_O (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
Quiescent Device Current	I_{CC}	V_{CC} or GND	0	6	-	-	8	-	80	-	160	µA
HCT TYPES												
High Level Input Voltage	V_{IH}	-	-	4.5 to 5.5	2	-	-	2	-	2	-	V
Low Level Input Voltage	V_{IL}	-	-	4.5 to 5.5	-	-	0.8	-	0.8	-	0.8	V
High Level Output Voltage CMOS Loads	V_{OH}	V_{IH} or V_{IL}	-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
High Level Output Voltage TTL Loads			-4	4.5	3.98	-	-	3.84	-	3.7	-	V
Low Level Output Voltage CMOS Loads	V_{OL}	V_{IH} or V_{IL}	0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			4	4.5	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I_I	V_{CC} to GND	0	5.5	-	-	±0.1	-	±1	-	±1	µA
Quiescent Device Current	I_{CC}	V_{CC} or GND	0	5.5	-	-	8	-	80	-	160	µA
Additional Quiescent Device Current Per Input Pin: 1 Unit Load (Note 4)	ΔI_{CC}	V_{CC} -2.1	-	4.5 to 5.5	-	100	360	-	450	-	490	µA

NOTE:

4. For dual-supply systems theoretical worst case (V_I = 2.4V, V_{CC} = 5.5V) specification is 1.8mA.

HCT Input Loading Table

INPUT	UNIT LOADS
DS, D0-D7	0.2
$\overline{PE}$	0.35
CP, $\overline{CE}$	0.5
$\overline{MR}$	0.2

NOTE: Unit Load is ΔI_{CC} limit specified in DC Electrical Specifications table, e.g., 360µA max at 25°C.

Prerequisite For Switching Specifications

PARAMETER	SYMBOL	V_{CC} (V)	25°C		-40°C TO 85°C		-55°C TO 125°C		UNITS
			MIN	MAX	MIN	MAX	MIN	MAX	
HC TYPES									
Clock Frequency (Figure 1)	f_{MAX}	2	6	-	5	-	4	-	MHz
		4.5	30	-	25	-	20	-	MHz
		6	35	-	29	-	23	-	MHz

Prerequisite For Switching Specifications (Continued)

PARAMETER	SYMBOL	V_{CC} (V)	25°C		-40°C TO 85°C		-55°C TO 125°C		UNITS
			MIN	MAX	MIN	MAX	MIN	MAX	
$\overline{MR}$ Pulse Width (Figure 1)	t_w	2	100	-	125	-	150	-	ns
		4.5	20	-	25	-	30	-	ns
		6	17	-	21	-	26	-	ns
Clock Pulse Width (Figure 1)	t_W	2	80	-	100	-	120	-	ns
		4.5	16	-	20	-	24	-	ns
		6	14	-	17	-	20	-	ns
Set-up Time Data and $\overline{CE}$ to Clock (Figure 5)	t_{SU}	2	80	-	100	-	120	-	ns
		4.5	16	-	20	-	24	-	ns
		6	14	-	17	-	20	-	ns
Hold Time Data to Clock (Figure 5)	t_H	2	1	-	1	-	1	-	ns
		4.5	1	-	1	-	1	-	ns
		6	1	-	1	-	1	-	ns
Removal Time $\overline{MR}$ to Clock (Figure 5)	t_{REM}	2	0	-	0	-	0	-	ns
		4.5	0	-	0	-	0	-	ns
		6	0	-	0	-	0	-	ns
Set-up Time $\overline{PE}$ to CP (Figure 5)	t_{SU}	2	145	-	180	-	220	-	ns
		4.5	29	-	36	-	44	-	ns
		6	25	-	31	-	38	-	ns
Hold Time $\overline{PE}$ to CP or $\overline{CE}$ (Figure 5)	t_H	2	0	-	0	-	0	-	ns
		4.5	0	-	0	-	0	-	ns
		6	0	-	0	-	0	-	ns
HCT TYPES									
Clock Frequency (Figure 2)	f_{MAX}	4.5	25	-	20	-	16	-	MHz
$\overline{MR}$ Pulse Width (Figure 2)	t_w	4.5	35	-	44	-	53	-	ns
Clock Pulse Width (Figure 2)	t_w	4.5	20	-	25	-	30	-	ns
Set-up Time Data and $\overline{CE}$ to Clock (Figure 6)	t_{SU}	4.5	16	-	20	-	24	-	ns
Hold Time Data to Clock (Figure 6)	t_H	4.5	0	-	0	-	0	-	ns
Removal Time $\overline{MR}$ to Clock (Figure 6)	t_{REM}	4.5	0	-	0	-	0	-	ns
Set-up Time $\overline{PE}$ to CP (Figure 6)	t_{SU}	4.5	30	-	38	-	45	-	ns
Hold Time $\overline{PE}$ to CP or $\overline{CE}$ (Figure 6)	t_H	4.5	0	-	0	-	0	-	ns

Switching Specifications Input t_r, t_f = 6ns

PARAMETER	SYMBOL	TEST CONDITIONS	V_{CC} (V)	25°C		-40°C TO 85°C	-55°C TO 125°C	UNITS
				TYP	MAX	MAX	MAX	
HC TYPES								
Propagation Delay, Clock to Output (Figure 3)	t_{PLH}, t_{PHL}	C_L = 50pF	2	-	160	200	240	ns
			4.5	-	32	40	48	ns
		C_L = 15pF	5	13	-	-	-	ns
		CL = 50pF	6	-	27	34	41	ns

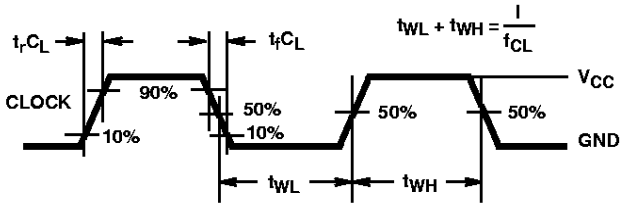
Switching Specifications Input t_r, t_f = 6ns **(Continued)**

PARAMETER	SYMBOL	TEST CONDITIONS	V_{CC} (V)	25°C TYP	25°C MAX	-40°C TO 85°C MAX	-55°C TO 125°C MAX	UNITS
Output Transition Time (Figure 3)	t_{TLH}, t_{THL}	C_L = 50pF	2	-	75	95	110	ns
			4.5	-	15	19	22	ns
			6	-	13	16	19	ns
Propagation Delay MR to Output (Figure 3)	t_{PHL}	C_L = 50pF	2	-	160	200	240	ns
			4.5	-	32	40	48	ns
			6	-	27	34	41	ns
Input Capacitance	C_I	-	-	-	10	10	10	pF
Power Dissipation Capacitance (Notes 5, 6)	C_{PD}	-	5	41	-	-	-	pF
HCT TYPES								
Propagation Delay, Clock to Output (Figure 4)	t_{PLH}, t_{PHL}	C_L = 50pF	4.5	-	40	50	60	ns
Output Transition Time (Figure 4)	t_{TLH}, t_{THL}	C_L = 50pF	4.5	-	15	19	22	ns
Propagation Delay $\overline{MR}$ to Output (Figure 4)	t_{PHL}	C_L = 50pF	4.5	-	40	50	60	ns
Input Capacitance	C_I	-	-	-	10	10	10	pF

NOTES:

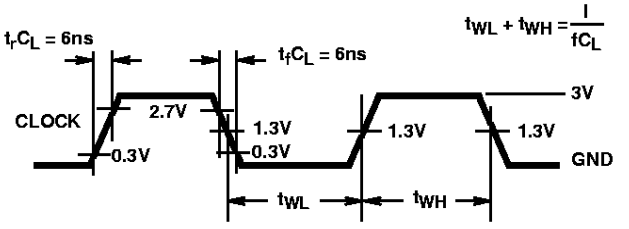
5. C_{PD} is used to determine the dynamic power consumption, per gate.
6. $P_D = C_{PD} V_{CC}^2 f_i + \Sigma (C_L V_{CC}^2 + f_O)$ where f_i = Input Frequency, f_O = Output Frequency, C_L = Output Load Capacitance, V_{CC} = Supply Voltage.

Test Circuits and Waveforms



NOTE: Outputs should be switching from 10% V_{CC} to 90% V_{CC} in accordance with device truth table. For f_{MAX}, input duty cycle = 50%.

FIGURE 1. HC CLOCK PULSE RISE AND FALL TIMES AND PULSE WIDTH



NOTE: Outputs should be switching from 10% V_{CC} to 90% V_{CC} in accordance with device truth table. For f_{MAX}, input duty cycle = 50%.

FIGURE 2. HCT CLOCK PULSE RISE AND FALL TIMES AND PULSE WIDTH

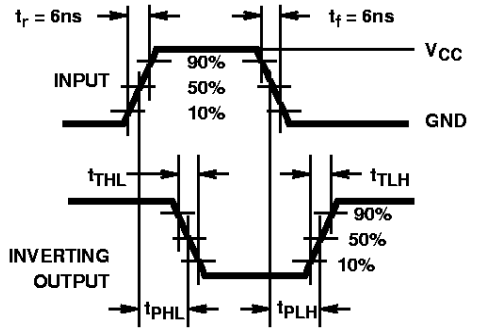


FIGURE 3. HC AND HCU TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

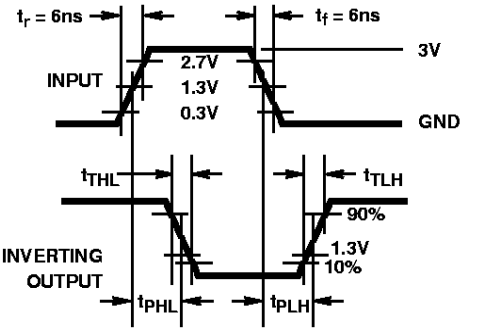


FIGURE 4. HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

Test Circuits and Waveforms (Continued)

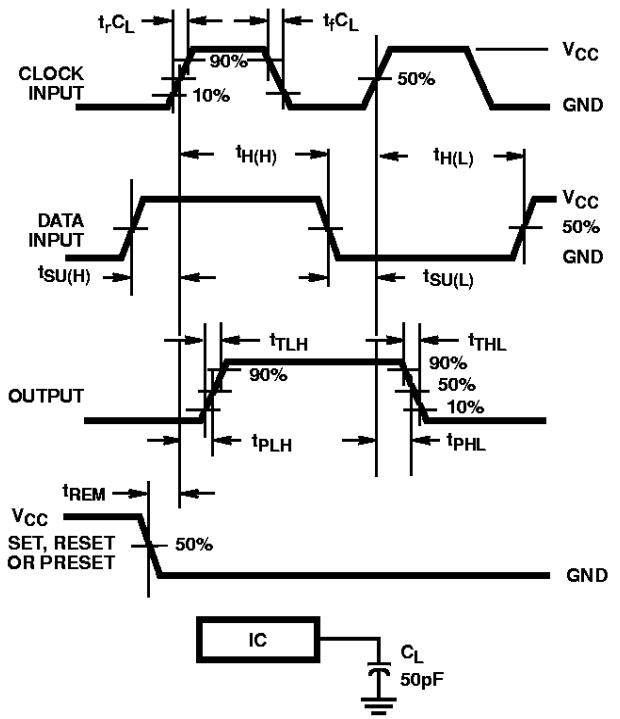


FIGURE 5. HC SETUP TIMES, HOLD TIMES, REMOVAL TIME, AND PROPAGATION DELAY TIMES FOR EDGE TRIGGERED SEQUENTIAL LOGIC CIRCUITS

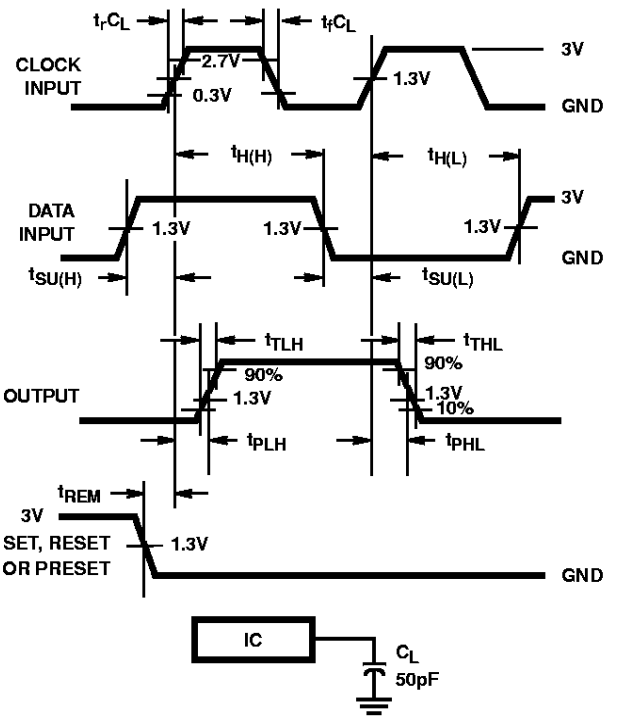


FIGURE 6. HCT SETUP TIMES, HOLD TIMES, REMOVAL TIME, AND PROPAGATION DELAY TIMES FOR EDGE TRIGGERED SEQUENTIAL LOGIC CIRCUITS

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